

## 1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

## 3. Applications

- AC Fan controller
- General purpose low power phase control
- General purpose low power switching

## 4. Quick reference data

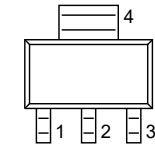
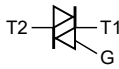
Table 1. Quick reference data

| Symbol                        | Parameter                            | Conditions   | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------------|--|-----|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |  | -   | -   | 600 | V    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_{sp} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a> | -   | -   | 0.8 | A    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>  | -   | -   | 9   | A    |
|                               |                                      | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$  | -   | -   | 10  | A    |
| $T_j$                         | junction temperature                 |  | -   | -   | 125 | °C   |
| <b>Static characteristics</b> |                                      |  |     |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                     | -   | 1   | 5   | mA   |
|                               |                                      | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                     | -   | 2   | 5   | mA   |

| Symbol                         | Parameter                             | Conditions  | Min | Typ  | Max | Unit             |
|--------------------------------|---------------------------------------|---|-----|------|-----|------------------|
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 9                                       | -   | 2    | 5   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; Fig. 9                                       | -   | 4    | 7   | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 11  | -   | 1    | 10  | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 0.85\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 12  | -   | 1.35 | 1.6 | V                |
| <b>Dynamic characteristics</b> |                                       |   |     |      |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | 30  | 45   | -   | V/ $\mu\text{s}$ |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 600\text{ V}$ ; $T_j = 50\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 0.3\text{ A/ms}$ ; $I_T = 0.84\text{ A}$ ; gate open circuit   | -   | 5    | -   | V/ $\mu\text{s}$ |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description     | Simplified outline  | Graphic symbol  |
|-----|--------|-----------------|---|---|
| 1   | T1     | main terminal 1 |  <p>SC-73 (SOT223)</p> |  <p>sym051</p> |
| 2   | T2     | main terminal 2 |   |   |
| 3   | G      | gate            |   |   |
| 4   | T2     | main terminal 2 |   |   |

## 6. Ordering information

Table 3. Ordering information

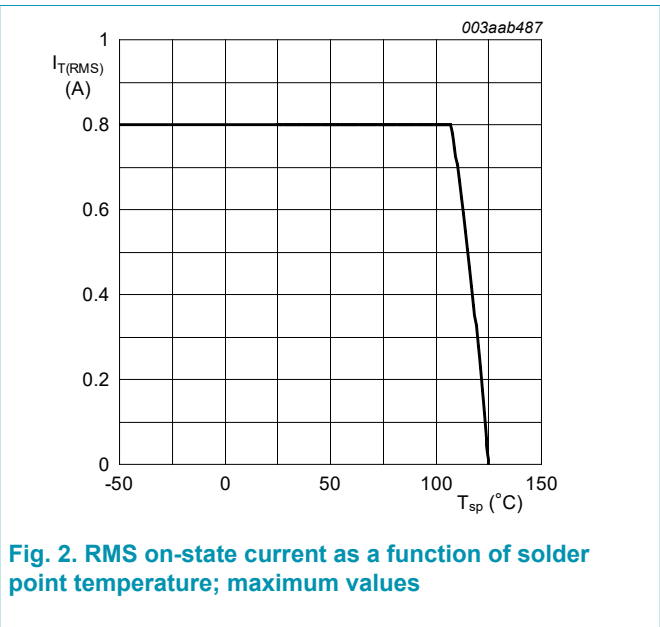
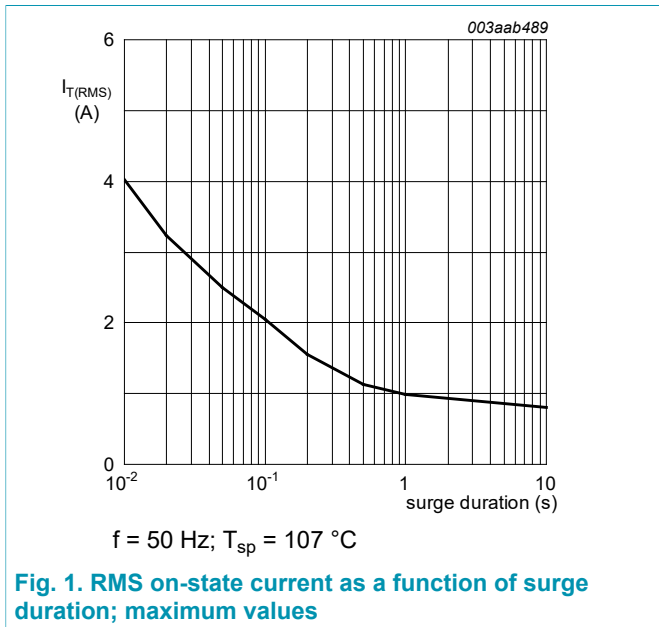
| Type number  | Package |  |         |
|--------------|---------|--|---------|
|              | Name    | Description  | Version |
| BT1308W-600D | SC-73   | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |

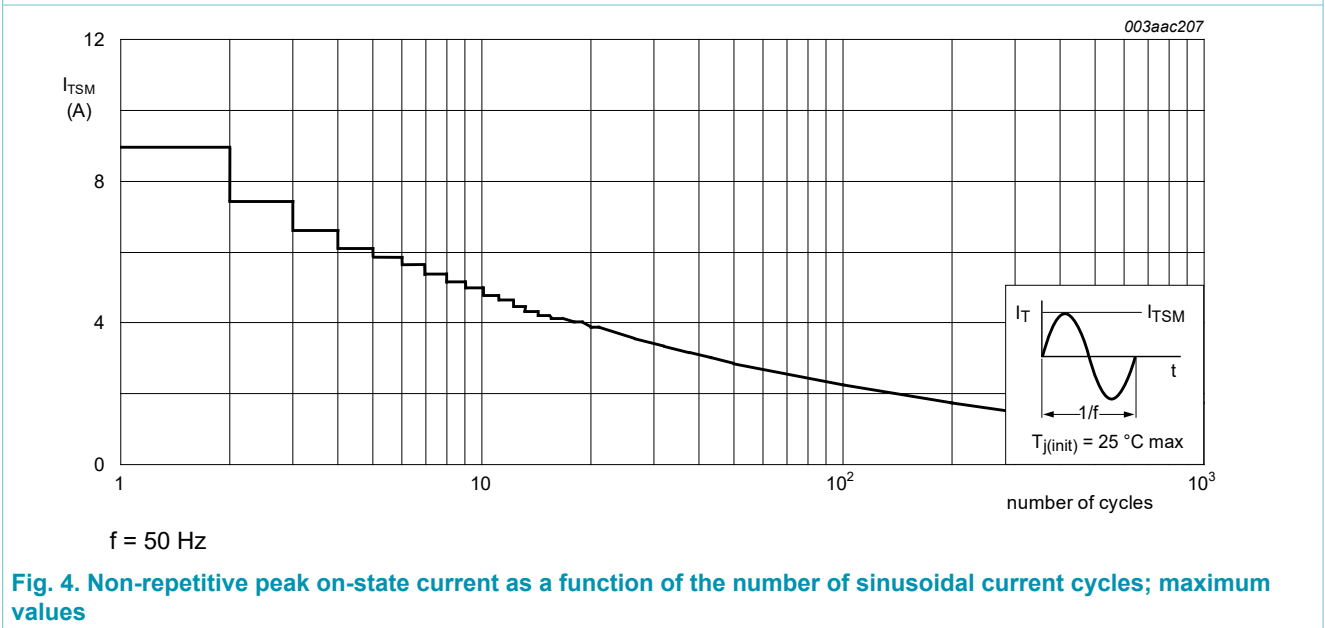
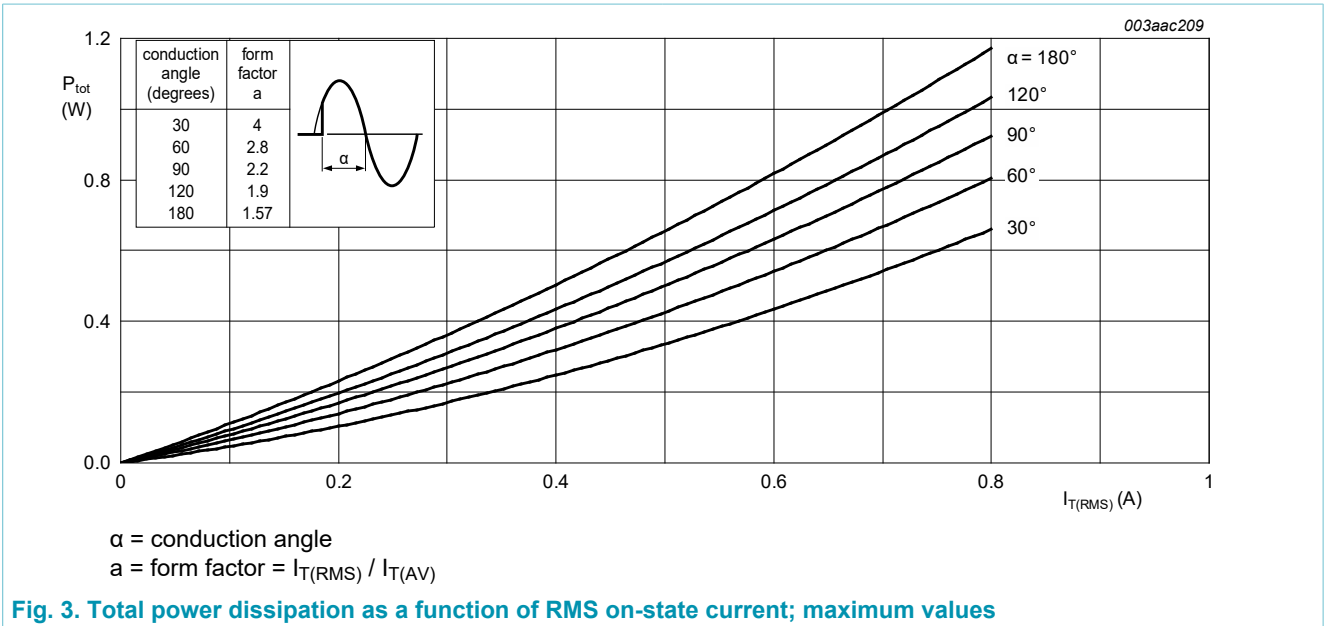
## 7. Limiting values

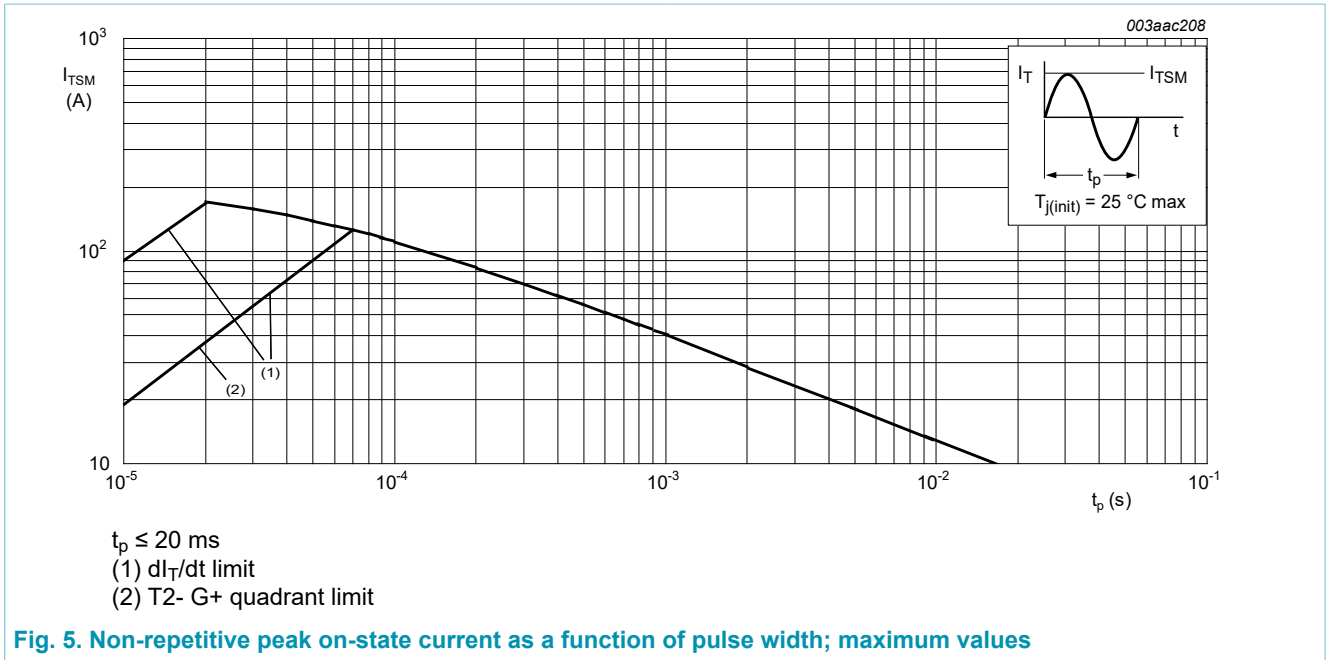
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions   | Min | Max  | Unit             |
|--------------|--------------------------------------|--|-----|------|------------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |  | -   | 600  | V                |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{sp} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>       | -   | 0.8  | A                |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 9    | A                |
|              |                                      | full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$   | -   | 10   | A                |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN   | -   | 0.32 | A <sup>2</sup> s |
| $di_T/dt$    | rate of rise of on-state current     | $I_G = 20\text{ mA}$ ; T2+ G+  | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2+ G-  | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2- G-  | -   | 50   | A/ $\mu$ s       |
|              |                                      | $I_G = 20\text{ mA}$ ; T2- G+  | -   | 10   | A/ $\mu$ s       |
| $I_{GM}$     | peak gate current                    |  | -   | 1    | A                |
| $P_{GM}$     | peak gate power                      |  | -   | 5    | W                |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period  | -   | 0.1  | W                |
| $T_{stg}$    | storage temperature                  |  | -40 | 150  | °C               |
| $T_j$        | junction temperature                 |  | -   | 125  | °C               |







## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol         | Parameter  | Conditions  | Min | Typ | Max | Unit |
|----------------|--|---|-----|-----|-----|------|
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point     | full cycle; <a href="#">Fig. 6</a>                        | -   | -   | 15  | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient free air | full cycle; for minimum footprint; <a href="#">Fig. 7</a> | -   | 156 | -   | K/W  |
|                |  | full cycle; for pad area; <a href="#">Fig. 8</a>          | -   | 70  | -   | K/W  |

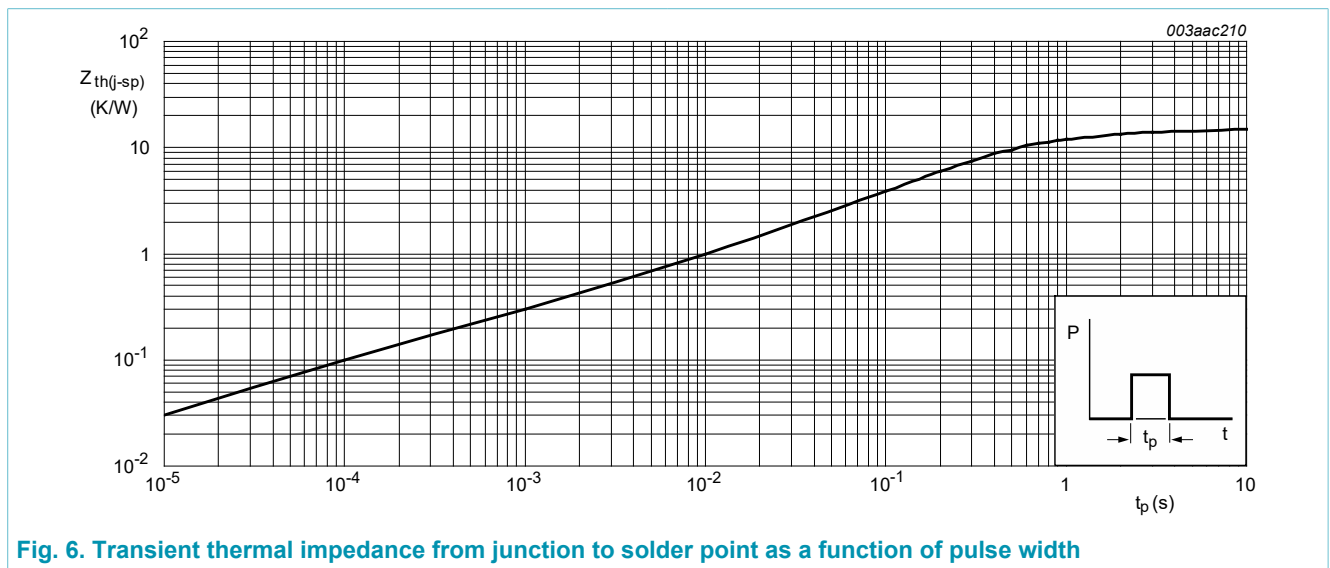
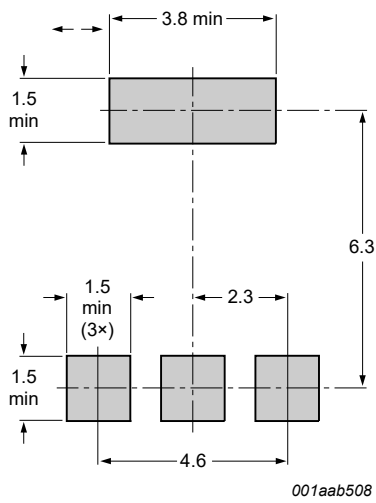
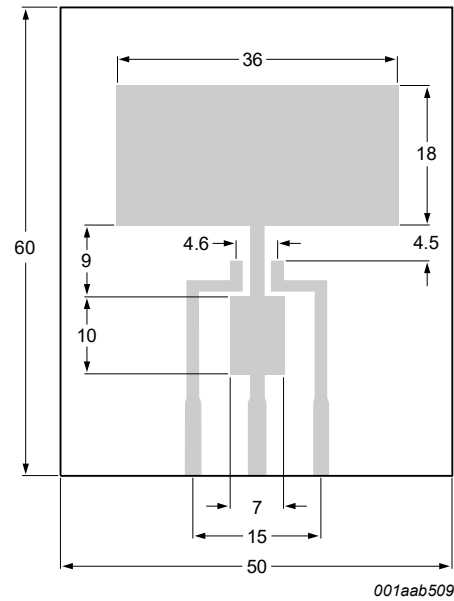


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



All dimensions are in mm

Fig. 7. Minimum footprint SOT223



All dimensions are in mm

Printed circuit board:

FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

Fig. 8. Printed circuit board pad area: SOT223

## 9. Characteristics

Table 6. Characteristics

| Symbol                         | Parameter                             | Conditions  | Min | Typ  | Max | Unit       |
|--------------------------------|---------------------------------------|---|-----|------|-----|------------|
| <b>Static characteristics</b>  |                                       |   |     |      |     |            |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                       | -   | 1    | 5   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                       | -   | 2    | 5   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                       | -   | 2    | 5   | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>                       | -   | 4    | 7   | mA         |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>                      | -   | 1    | 10  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>                      | -   | 5    | 10  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>                      | -   | 1    | 10  | mA         |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+;<br>$T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>                      | -   | 2    | 10  | mA         |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>  | -   | 1    | 10  | mA         |
| $V_T$                          | on-state voltage                      | $I_T = 0.85\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>  | -   | 1.35 | 1.6 | V          |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ;<br><a href="#">Fig. 13</a>                              | -   | 0.9  | 1.5 | V          |
|                                |                                       | $V_D = 600\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 110\text{ °C}$ ;<br><a href="#">Fig. 13</a>                            | 0.1 | 0.7  | -   | V          |
| $I_D$                          | off-state current                     | $V_D = 600\text{ V}$ ; $T_j = 125\text{ °C}$  | -   | 0.1  | 0.5 | mA         |
| <b>Dynamic characteristics</b> |                                       |   |     |      |     |            |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 402\text{ V}$ ; $T_j = 110\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit | 30  | 45   | -   | V/ $\mu$ s |
| $dV_{com}/dt$                  | rate of change of commutating voltage | $V_D = 600\text{ V}$ ; $T_j = 50\text{ °C}$ ; $dI_{com}/dt = 0.3\text{ A/ms}$ ; $I_T = 0.84\text{ A}$ ; gate open circuit   | -   | 5    | -   | V/ $\mu$ s |
| $t_{gt}$                       | gate-controlled turn-on time          | $I_{TM} = 1\text{ A}$ ; $V_D = 600\text{ V}$ ; $I_G = 25\text{ mA}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$                    | -   | 2    | -   | $\mu$ s    |



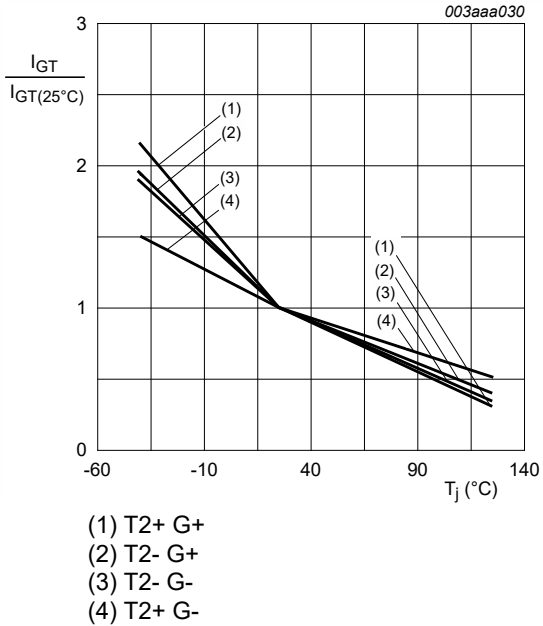


Fig. 9. Normalized gate trigger current as a function of junction temperature

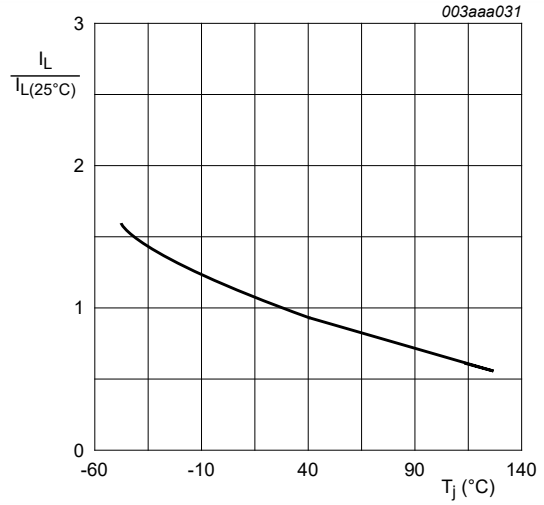


Fig. 10. Normalized latching current as a function of junction temperature

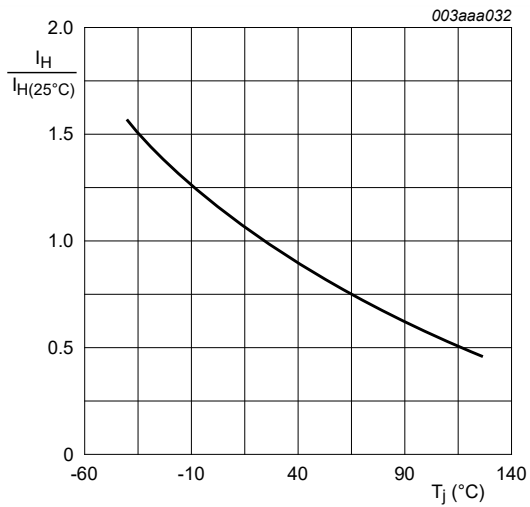
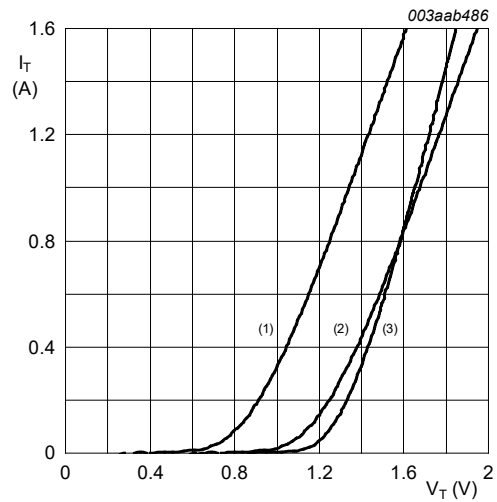


Fig. 11. Normalized holding current as a function of junction temperature



$V_o = 1.171\text{ V}; R_s = 0.5125\ \Omega$   
 (1)  $T_j = 125^\circ\text{C}$ ; typical values  
 (2)  $T_j = 125^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25^\circ\text{C}$ ; maximum values

Fig. 12. On-state current as a function of on-state voltage

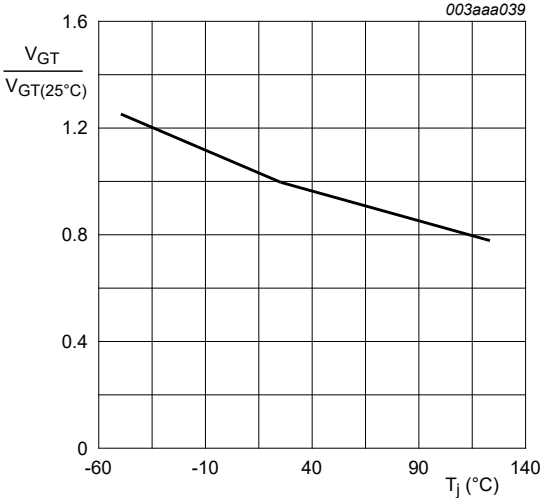


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

### 10. Package outline

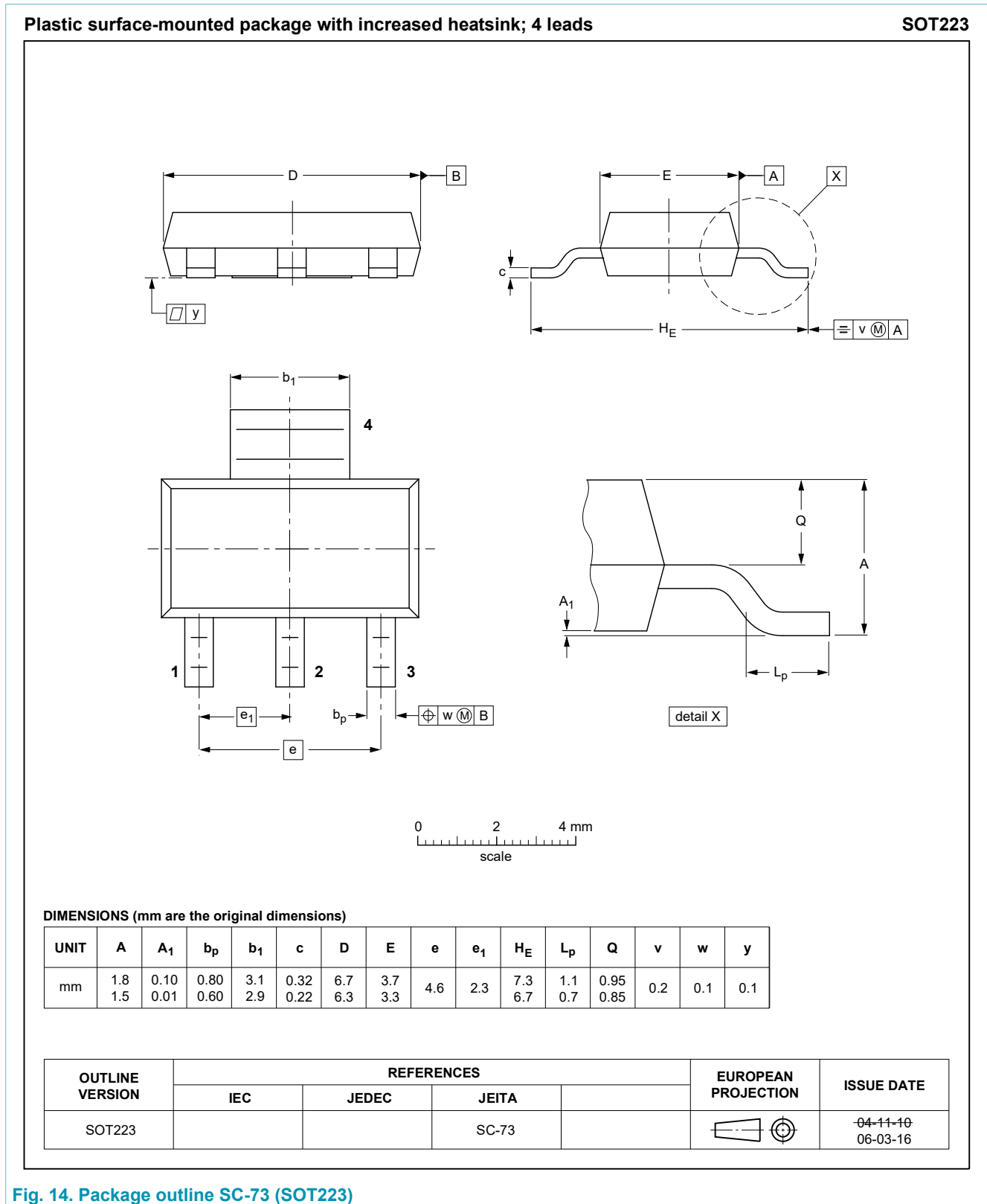


Fig. 14. Package outline SC-73 (SOT223)

# 11. Legal information

## Data sheet status

| Document status [1][2]         | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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- [1] Please consult the most recently issued document before initiating or completing a design.
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Date of release: 15 September 2018

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